Preferred Device

Power MOSFET 750 mAmps, 20 Volts

P-Channel SOT-23

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc–dc converters and power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low R_{DS(on)} Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb-Free Package is Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	20	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
Drain Current - Continuous @ T _A = 25°C - Pulsed Drain Current (t _p ≤ 10 μs)	I _D	750 2000	mA
Total Power Dissipation @ T _A = 25°C	P_{D}	400	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°Ç
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	300	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_{L}	260	å

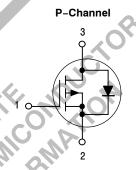
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



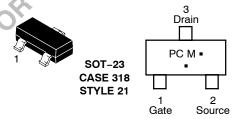
ON Semiconductor®

http://onsemi.com

750 mAMPS, 20 VOLTS $R_{DS(on)} = 350 \text{ m}\Omega$



MARKING DIAGRAM/ PIN ASSIGNMENT



PC = Device Code M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MGSF1P02LT1	SOT-23	3000/Tape & Reel
MGSF1P02LT1G	SOT-23 Pb-Free	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

C	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS					•		
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 10 μAdc)			20	_	-	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 20 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$ $(V_{DS} = 20 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, T_{J} = 125^{\circ}\text{C})$			- -	- -	1.0 10	μAdc	
Gate-Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)			-	-	±100	nAdc	
ON CHARACTERISTICS (Note 1)		1					
Gate Threshold Voltage (V _{DS} = V _{GS} ,	I _D = 250 μAdc)	V _{GS(th)}	1.0	1.7	2.4	Vdc	
Static Drain-to-Source On-Resistance $(V_{GS} = 10 \text{ Vdc}, I_D = 1.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 0.75 \text{ Adc})$			- -	0.235 0.375	0.350 0.500	Ω	
DYNAMIC CHARACTERISTICS							
Input Capacitance	(V _{DS} = 5.0 Vdc)	C _{iss}	-	130	_	pF	
Output Capacitance	(V _{DS} = 5.0 Vdc)	C _{oss}	_	120	% -		
Transfer Capacitance	(V _{DG} = 5.0 Vdc)	C _{rss}	-	60	_		
SWITCHING CHARACTERISTICS (Note 2)							
Turn-On Delay Time		t _{d(on)}		2.5	-	ns	
Rise Time	$(V_{DD} = 15 \text{ Vdc}, I_D = 1.0 \text{ Adc},$	t _r	3 .	1.0	-		
Turn-Off Delay Time	$R_L = 50 \Omega$)	t _{d(off)}	-	16	-		
Fall Time	CO	t _f	17	8.0	-		
Gate Charge (See Figure 6)	95	Q _T	-	6000	-	рC	
SOURCE-DRAIN DIODE CHARACT	ERISTICS	2 70					
Continuous Current	13 01	Is	_	_	0.6	Α	
Pulsed Current	CV .OQ	I _{SM}	_	-	0.75	-	
Forward Voltage (Note 2)	110,01,0	V _{SD}	-	1.5	-	V	

- Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

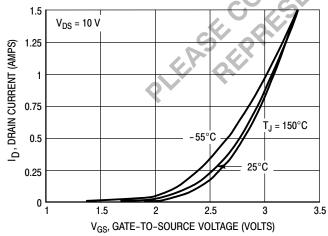


Figure 1. Transfer Characteristics

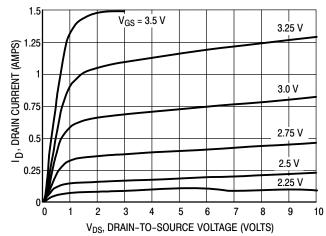


Figure 2. On-Region Characteristics

TYPICAL ELECTRICAL CHARACTERISTICS

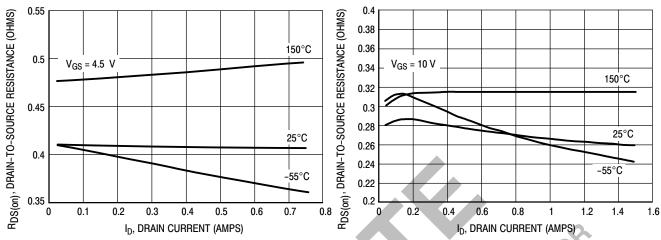


Figure 3. On-Resistance versus Drain Current

Figure 4. On-Resistance versus Drain Current

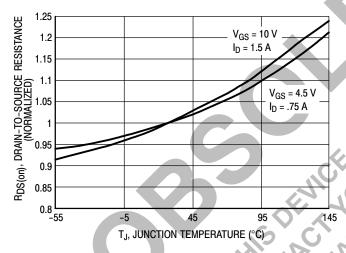


Figure 5. On-Resistance Variation with Temperature

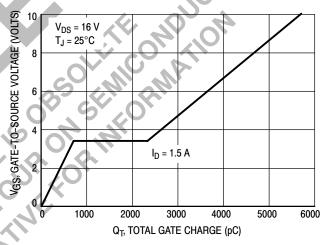


Figure 6. Gate Charge

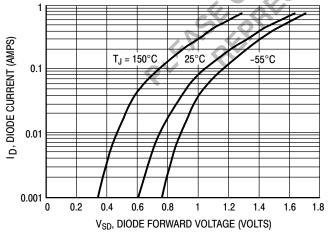


Figure 7. Body Diode Forward Voltage

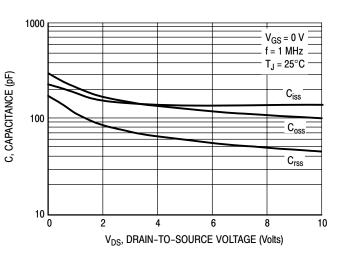
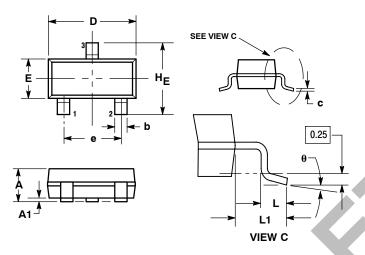


Figure 8. Capacitance

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES

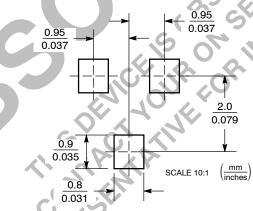
- LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 1. 318-01 THRU -07 AND -09 OBSOLETE,
- NEW STANDARD 318-08

	MILLIMETERS			INCHES		
DIM	MIN.	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	_0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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